NSN 5961-00-411-2013



Diode Semiconductor Device - Page 1 of 1 View Online at https://aerobasegroup.com/nsn/5961-00-411-2013 **Inclosure Material:** Metal **Overall Length:** 1.253 inches **Mounting Facility Quantity: Mounting Method:** Threaded stud **Overall Width Across Flats:** Between 0.424 inches and 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 6.8 regulator voltage **Voltage Tolerance In Percent:** -5.0/+5.0**Current Rating Per Characteristic:** 370.00 milliamperes all primaries horsepower metric and 1.50 amperes repetitive peak forward current **Power Rating Per Characteristic:** 10.0 watts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 1 tab, solder lug **Specification Data:** 81349-mil-prf-19500/124 government specification Shelf Life: N/a **Unit Of Measure:**

Demilitarization:

No

Fiig:

A110a0

Mil-std (military Standard):

Mil-prf-19500 spec.